

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. FETHE24.001CP1	APPLICATION NO. 10/005,186
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		RECEIVED	
(USE SEVERAL SHEETS IF NECESSARY)		APPLICANTS Camm, et al.	MAY 22 2002
		FILING DATE December 4, 2001	GROUP ART UNIT 3742 TECHNOLOGY CENTER RS700

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1,587,023	06/01/66	Mottlau			
	24,296 RE	03/26/57	Stewart			
	2,981,819	04/25/61	Gregory			
	3,047,438	07/31/62	Marinace			
	3,108,713	10/22/63	Barrett, et al.			
	3,160,517	12/08/64	Jenkin			
	3,188,459	06/08/65	Bridwell			
	3,227,065	01/04/66	Litman			
	3,239,651	03/08/66	Silberman			
	3,240,915	03/15/66	Carter, et al.			
	3,460,510	08/12/69	Currin			
	3,502,516	03/24/70	Henker			
	3,623,712	11/30/71	McNeilly, et al.			
	3,627,590	12/14/71	Mammel			
	3,661,637	04/09/72	Sirtl			
	3,692,572	09/19/72	Strehlow			
	3,836,751	09/17/74	Anderson			
	3,913,872	10/21/75	Weber			
	4,041,278	08/09/77	Boah			
	4,081,313	03/28/78	McNeilley, et al.			
	4,097,226	06/27/78	Erikson, et al.			
	4,101,759	07/18/78	Anthony, et al.			
	4,115,163	09/19/78	Gorina, et al.			
	4,151,008	04/24/79	Kirkpatrick			
	4,164,643	08/14/79	Pearl, et al.			
	4,220,483	09/02/80	Cazcarra			
	4,224,096	09/23/80	Osborne			

EXAMINER	Shawntea Fugua	DATE CONSIDERED	3/7/04
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	4,233,493	11/11/80	Nath			
<i>Gf</i>	4,308,078	12/29/81	Cook			
	4,315,130	02/09/82	Inagaki, et al.			
	4,331,485	05/25/82	Gat			
	4,370,175	01/25/83	Levatter			
	4,375,993	03/08/83	Mori, et al.			
	4,379,727	04/12/83	Hansen, et al.			
	4,398,094	08/9/83	Hiramoto			
	4,421,048	12/20/83	Adema, et al.			
	4,431,459	02/14/84	Teng			
	4,455,479	06/19/84	Itoh, et al.			
	4,493,977	01/15/85	Arai, et al.			
	4,533,820	08/06/85	Shimizu			
	4,539,431	09/03/85	Moddel, et al.			
	4,540,876	09/10/85	McGinty			
	4,550,245	10/29/85	Arai, et al.			
	4,550,684	11/05/85	Mahawili			
	4,567,352	01/28/86	Mimura, et al.			
	4,649,261	03/10/87	Sheets			
	4,680,447	07/14/87	Mahawili			
	4,698,486	10/06/87	Sheets			
	5,219,786	06/15/93	Noguchi			
	5,336,641	08/09/94	Fair, et al.			
	5,399,506	03/21/95	Tsukamoto			
<i>V</i>	5,446,825	08/29/95	Mosleh, et al.			
<i>Gf</i>	5,908,307	06/01/99	Talwar, et al.			
	6,051,483	04/18/00	Lee, et al.			

EXAMINER <i>Shaundina Fugue</i>	DATE CONSIDERED 3/7/04
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	FILING DATE December 4, 2001	GROUP ART UNIT 3742
		RECEIVED MAY 22 2002 TECHNOLOGY CENTER R3700

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>SJF</i>	32864	08/08/21	Norway				
	938,699	12/16/60	United Kingdom				
	55-115327 (Abstract)	09/05/80	Japan				
	56-48128 (Abstract)	05/1/81	Japan				
	2065973A	07/01/81	United Kingdom				
	0080729 (Abstract)	05/20/82	Japan				
	57-208146 (Abstract)	12/21/82	Japan				
<i>VV</i>	02294027A	05/12/90	Japan				
	0 399 662 A2	11/28/90	European				
<i>SJF</i>	WO 00/67298	11/09/00	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>SJF</i>	J. Lue, "Arc Annealing of BF+2 Implanted Silicon by a Short Pulse Flash Lamp," Appl. Phys. Lett., Volume 36, No. 1, pp. 73-76, dated January 1, 1980.
	M. Lefrancois and D. Camm, "Temperature Uniformity During Impulse Anneal," 8th International Conference on Advanced Thermal Processing of Semiconductors, RTP 2000, pp. 1-6, dated September 20-22, 2000.
	A.T. Fiory, K.K. Bourdelle, P.K. Roy and S.P. McCoy, "Spike Annealing of Implanted PMOS Gates," Proc. of RTP 2000 Conference, pp. 1-8, dated September 20-22, 2000.
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	"Searchlight Model-100," Tamarack Scientific Co., Inc.
	A.R. Lunde, "Nasa Tech Brief," B75-1008, Lewis Research Center, dated April 1975.
	"Transient Calorimeter Calibration System," AFFDL-TR-75-24, Tamarack Scientific Company, Orange, California, pp. 1-50, dated March 1975.
<i>VV</i>	N.S. Kapany, J.A. Eyer and R.E. Keim, "Fiber Optics. Part II. Image Transfer on Static and Dynamic Scanning with Fiber Bundles," Journal of the Optical Society of America, Volume 47, No. 5, pp. 423-427, dated May 1957.
	R. J. Potter, "Transmission Properties of Optical Fibers," Journal of the Optical Society of America, Volume 51, No. 10, pp. 1079-1089, dated October 1961.

EXAMINER <i>Charlene Tague</i>	DATE CONSIDERED <i>3/7/04</i>
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EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	D. E. Williamson, "Cone Channel Condenser Optics," Journal of the Optical Society of America, Volume 42, No. 10, pp. 712-715, dated October 1952.
	R.L. Cohen, J.S. Williams, L.C. Feldman and K.W. West, Thermally Assisted Flash Annealing of Silicon and Germanium, Bell Laboratories, Murray Hill, New Jersey, pp. 1-4.
	R.J. von Gutfeld, "Crystallization of Silicon for Solar Cell Applications," IBM Technical Disclosure, Volume 19, IBM Corp., pp. 3955-3956, dated March 1977.
	T.O. Sedgwick, "Short Time Annealing," J. Electrochem. Soc., Volume 130, No. 2, pp. 484-492, dated February 1983.
	P. S. Burggraaf, "Rapid Wafer Heating: Status 1983," Semiconductor International, pp. 69-74, dated December 1983.
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	M. Current and A. Yee, "Ion Implantation and Rapid Annealing of 125 mm Wafers," Solid State Technology, pp. 197-202, dated October 1983.
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	J.C. C. Fan, B-& Tsaur and M.W. Geis, "Transient Heating with Graphite Heaters for Semiconductor Processing," Laser and Electron-Beam Interactions with Solids, Elsevier Science Publishing Company, Inc., pp. 751-758 (1982).
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EXAMINER	Shawntina Fugna	DATE CONSIDERED	3/7/04
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O 1 INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i> 	Atty. Docket No. FETHE24.001CP1 (47753-5cip)	Serial No. 10/005,186
	Applicant(s) David Malcolm Camm; J. Kiefer Elliott	
	Filing Date December 4, 2001	Group 3742

PATENT & TRADE MARK

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER ART (*including Author, Title, Date, Pertinent Pages, Etc.*)

S/No	International Search Report for PCT/CA01/01706 (2 pages).
	RECEIVED JUL 1 2007 TECHNOLOGY CENTER 2800
EXAMINER	DATE CONSIDERED

*EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>Sgt</i>	Tillmann, et al. "Processing of 200 and 300 mm Wafers in an Advanced Rapid Thermal Processing System," Proc RTP 1998, 6 th International Conference on Advanced Thermal Processing of Semiconductors, Kyoto, Japan, 1998, pp. 62-63.

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